

INSTRUMENT: HALL PROBE (Ge Crystal) # 5330

Specification of the material

Crystal	: n-type lightly doped
Hall Coefficient	: $20.7 \times 10^3 \text{ cm}^3 \text{ Coulomb}^{-1}$
Carrier Mobility	: $34.5 \times 10^2 \text{ cm}^2 \cdot \text{Volt}^{-1} \cdot \text{sec}^{-1}$
Carrier density	: $3.0 \times 10^{14} \text{ cm}^{-3}$
Resistivity	: $\cong 6 \text{ ohm. cm.}$

Details of the Hall Probe

Length & Width	: The distance between the respective probes
Thickness	: 0.50 mm
Maximum Current	: 10 mA
Input Current Leads	: Red & Black
Hall Voltage Output Leads	: Yellow & Green

Test Parameters

Input Current	: 8.00 mA
Offset Voltage	: < 1.0 mV
Hall Voltage	: 33.1 mV/8.0 mA/KG

**Measured by. Digital Hall Effect Set-up, DHE-21*

Passed for despatch : Yes

Dated : 12/03/2012

Q.C. Engineer: U.S. Chauhan

INSTRUMENT : HALL PROBE (Ge Crystal) # 5320

Specification of the Material

Crystal	:	p-type lightly doped
Hall Coefficient	:	$20.2 \times 10^3 \text{ cm}^3 \text{ Coulomb}^{-1}$
Carrier Mobility	:	$28.9 \times 10^2 \text{ cm}^2 \cdot \text{Volt}^{-1} \cdot \text{sec}^{-1}$
Carrier density	:	$3.1 \times 10^{14} \text{ cm}^{-3}$
Resistivity	:	$\cong 7 \text{ ohm. cm.}$

Details of the Hall Probe

Length & Width	:	The distance between the respective probes
Thickness	:	0.50 mm
Maximum Current	:	10 mA
Input Current Leads	:	Red & Black
Hall Voltage Output Leads	:	Yellow & Green

Test Parameters

Input Current	:	8.00 mA
Offset Voltage	:	< 1.0 mV
Hall Voltage	:	32.4 mV/8.0 mA/KG

**Measured by. Digital Hall Effect Set-up, DHE-2I*

Passed for dispatch : Yes

Dated : 12/03/2012

Q.C. Engineer: U.S. Chauhan